



#### **We3A-5**

# Impedance Standard Substrate Characterization and EM Model Definition for Cryogenic and Quantum-Computing Applications

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#### **Outline**



- Introduction and motivation
- Modelling of on-wafer calibration structures
  - Dimensions measurements
  - Cryo EM and mechanical characteristics of ISS
  - Load compensation method
- Measurement results
- Validation
- Conclusion

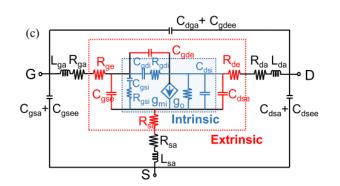


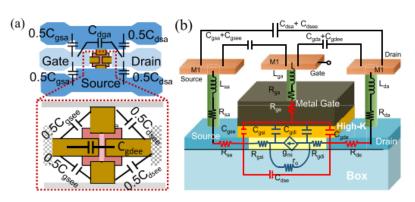


#### Introduction and motivation

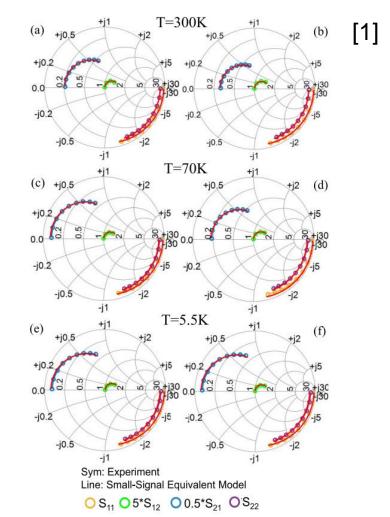


Cryogenic applications, such as quantum computing, is gathering more commercial interest, and cryogenic device modeling is an essential part of research progress which requires Wide-band measurements.





[1] Chakraborty, Wriddhi, et al. "Characterization and Modeling of 22 nm FDSOI Cryogenic RF CMOS." IEEE Journal on Exploratory Solid-State Computational Devices and Circuits 7.2 (2021): 184-192.



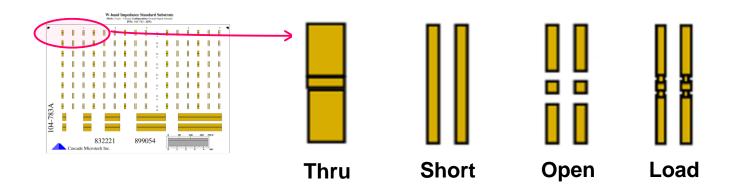




#### Introduction and motivation



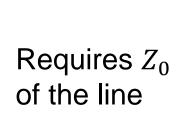
Wide-band calibration algorithms (e.g., SOLR) require knowledge of standards.

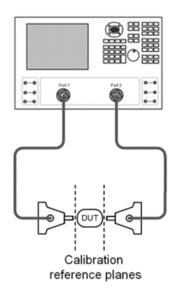


short

thru

Requires knowledge of standard





[1] Williams, Dylan F., et al. "Calibrations for millimeter-wave silicon transistor characterization." IEEE transactions on Microwave Theory and Techniques 62.3 (2014): 658-668.

600 μm

open

1500 µm

res





4000 μm

short

210 μm 70 μm short

9000 µm

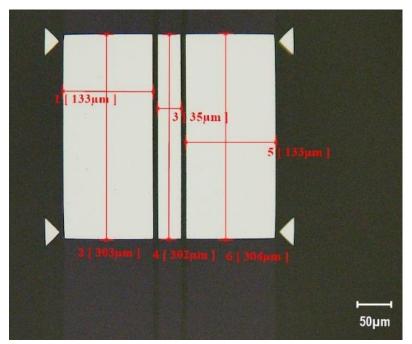
GSG



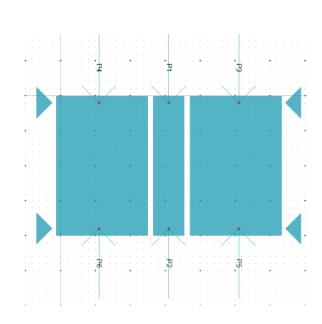
# Calibration structure modeling



Accurate models of calibration structures are made in ADS based on dimension measurements.



lateral dimensions using a microscope



Veeco Stylus profiler dektak 8 for layer height measurements





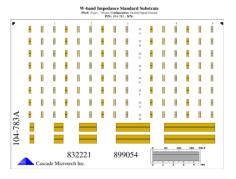
#### ISS characteristics



Two different ISS (Impedance Standard Substrate) are modelled in room temperature and 4K,Fused Quartz from IMS® and Alumina from FormFactor®

Substrate Material	Thermal contraction (\Delta L/L0) (293K to 4K)	Relative electrical permittivity	Loss tangent(ta n δ)	Top Metal
Alumina	0.063%	9.9	1e-4	GOLD(Au)
Fused Quartz	0.015%	3.81	4e-4	Aluminium(Al)





Alumina

Fused Quartz



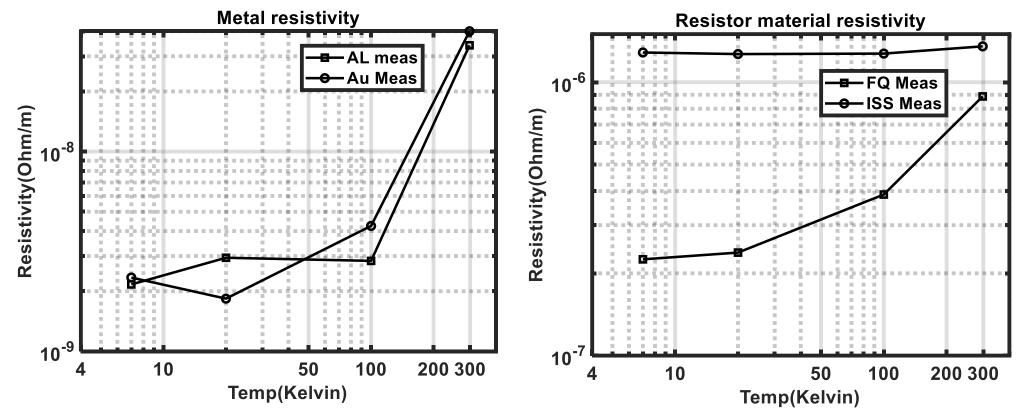




#### Materials characterization



In order to have accurate STD definitions, all the models are updated via new calculated dimensions and measured resistivity of conductive layers.



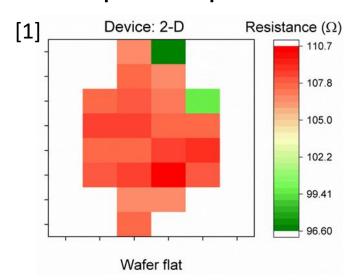


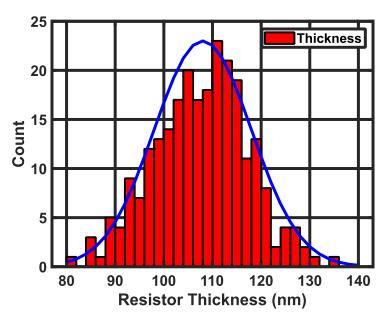


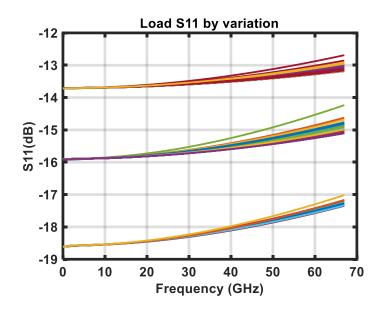
#### Process variation impact on load



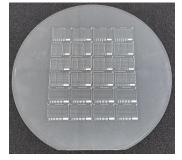
The impact of process variation is strongly noticeably on the load standard.







Resistors



[1] L. Galatro et al., "Towards Commercially Available Quartz Calibration Substrates," 2020 95th ARFTG Microwave Measurement Conference (ARFTG), 2020, pp. 1-5.







# **Load Compensation Algorithm**



Extract DC resistance of Load structure



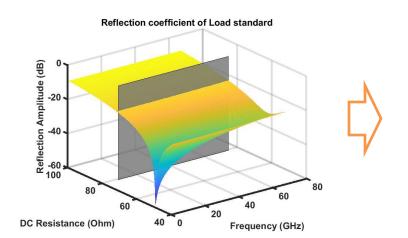
Extract DC resistance of Short structure

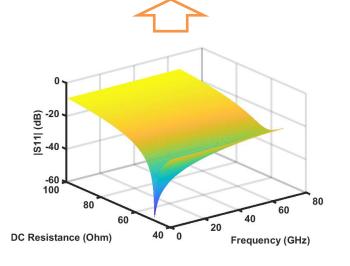


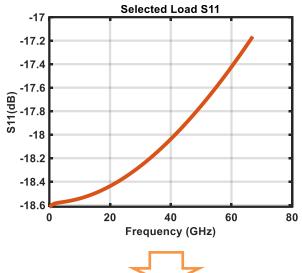
Calculate resistor value from difference



response from EM simulation dataset







Use the response as calibration standard



Calculate Error-terms



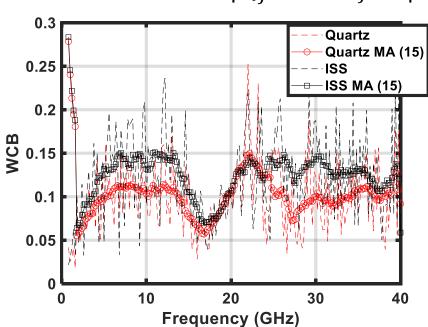


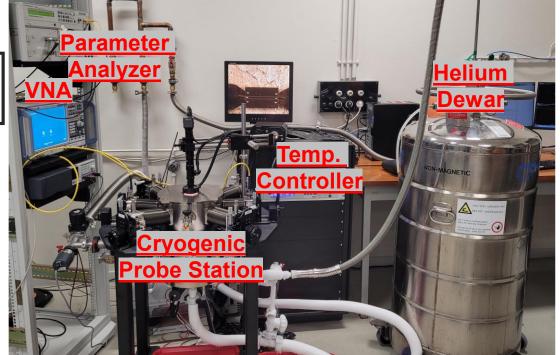
# Room temp. Calibration quality

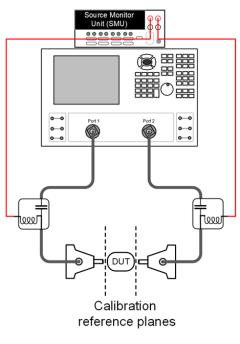


The room temperature behavior of the test-bench is acquired and used as a reference for the cryogenic measurements.

$$WCB(f) = max |S'_{ij}(f) - S_{ij}(f)|$$







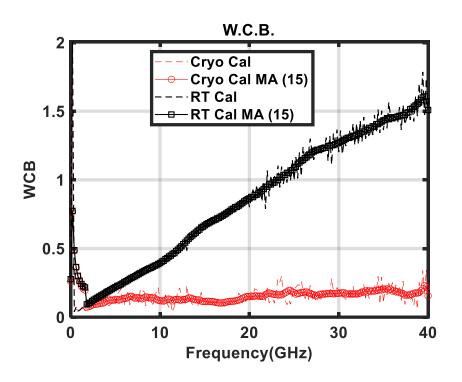


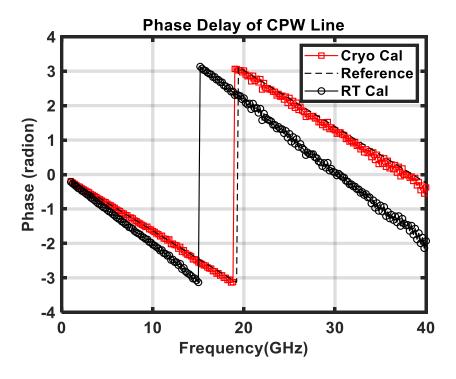


# Cryo measurement RT models vs Cryo models



WCB of CPW line on an <u>Alumina substrate</u> measured at 7K using calibration definition for the standards derived from RT response (RT – black line) and from cryogenic temperature responses (Cryo Cal – red line).







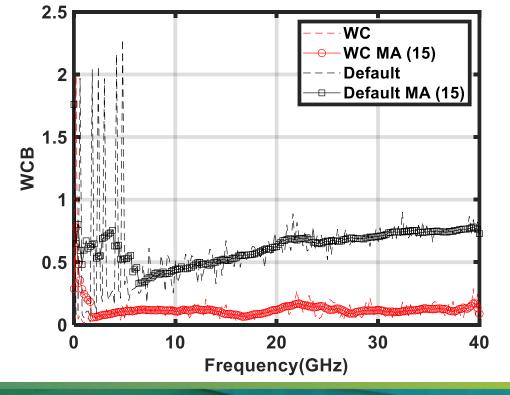


# Load compensated (Cryo) standards vs default (Cryo) standards



WCB on Fused Quartz substrate of a 1320 micron CPW on Quartz substrate using: (Default) calibration set employing default Cryo parameter response (i.e., nominal conductivity) and (WC) load response matching the measured device

DC resistivity.



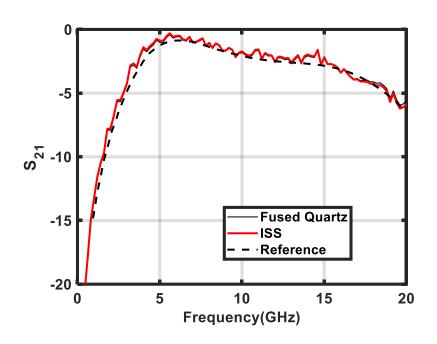


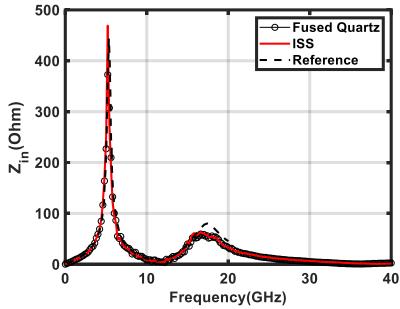


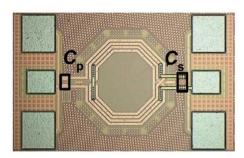
# Validation on a CMOS passive device



To verify, a transformer-based resonator with cryogenic model is measured [1] and corrected via both calibrations and compared.







transformer-based resonator realized in **CMOS** 

[1]B. Patra, M. Mehrpoo, A. Ruffino, F. Sebastiano, E. Charbon and M. Babaie, "Characterization and Analysis of On-Chip Microwave Passive Components at Cryogenic Temperatures," in IEEE Journal of the Electron Devices Society, vol. 8, pp. 448-456, 2020







#### Summary



- Discussed the necessity of cryogenic modelling of calibration structures
- Demonstrated modelling of two ISS structures based on measurements
- Introduced load compensation method to deal with process variation
- Demonstrated results of measurement
- Validation on a CMOS transformer-based resonator







### Thankyou for you attention





### Backup slide – stability



Gamma of an offset open was measured in Cryo setup at RT and in a reference setup to compare stability of setups.



